

SMBus NVDC Buck-Boost Charge Controller for 1- to 4-Cell Battery

FEATURES

- 1- to 4-Cell Charging from a Variety of Input Types
 - 3.58V to 24V Input Operating Voltage Range
 - USB 2.0/3.0/3.1 (Type-C)/USB PD Input Current Support
 - Seamless Buck ↔ Buck-Boost ↔ Boost Transitions
 - Input Overload Protection (IDPM and VDPM Regulation)
- CPU Throttling, Power and Current Monitoring
 - Full nPROCHOT Profile
 - · Input Current Monitoring
 - Battery Charge/Discharge Current Monitoring
 - System Power Monitoring
- Narrow Voltage DC (NVDC) Power Path Management
 - Instant-On with Depleted or No Battery
 - Battery Supplementation if Adapter is Fully Loaded
 - BATFET Ideal Diode Emulation in Supplement Mode
- Power-Up USB Port from Battery (USB OTG)
 - 3V to 20.56V Adjustable OTG Voltage with 8mV Resolution
 - Up to 6.35A Output Current Limit with 50mA Resolution
- Pass Through Mode (PTM) to Improve Efficiency
- V_{MIN} Active Protection (VAP) Mode
- VAP Supplements Battery from Input Caps for System Power Spikes (Battery-Only Conditions)
- Input Current Optimizer Maximizes Power Extraction
- 800kHz or 1.2MHz Selectable Switching Frequency
- SMBus Interface for Flexible System Configuration
- Input Current Limit Setting Pin (without SMBus)

• Integrated ADC for Voltage/Current/Power Monitoring

SGM41570

- Low Battery Quiescent Current
- High Accuracy
 - ±0.4% for Charge Voltage Regulation
 - ±2% for Input/Charge Current Regulation
 - ±2% for Input/Charge Current Monitor
 - + ±5.8% for Power Monitor
- Safety
 - Thermal Shutdown
 - Input/System/Battery Over-Voltage Protection
 - Input/MOSFET/Inductor Over-Current Protection
- Available in a Green TQFN-4×4-32AL Package

APPLICATIONS

Bluetooth Speakers, Drones, IP Cameras, Detachable Power Supply

Portable Internet Devices and Accessory Industrial and Medical Equipment

TYPICAL APPLICATION

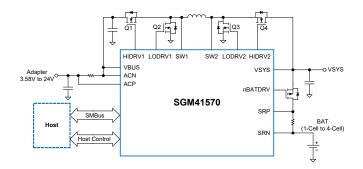


Figure 1. Typical Application Circuit

GENERAL DESCRIPTION

The SGM41570 is a synchronous Buck-Boost battery charge controller with NVDC power path management. It can provide high efficiency and low component count solution for 1-cell to 4-cell batteries charging applications.

The system is regulated slightly to be higher than the battery voltage, but not lower than the programmable system minimum voltage. Therefore, the system power is maintained even if the battery is completely depleted or removed. Dynamic power management (DPM) feature is also included that automatically reduces the charge current if the input current or voltage limit is reached. If the system load continues to increase after reduction of charge current down to zero, the battery enters the supplement mode and both adapter and battery power the system.

A wide range of input sources are supported for SGM41570, including traditional adapters, USB adapter and high voltage USB PD sources. The converter is configured as Buck, Boost or Buck-Boost during power-up, depending on the input source and battery conditions. The charger automatically switches among Buck, Boost and Buck-Boost without host control.

When the input source is absent, the SGM41570 can work in USB On-The-Go (OTG) mode to supply VBUS from battery. The OTG output voltage can be programmed from 3V to 20.56V with 8mV resolution. The slew rate of the output voltage transitions in OTG can be configured (by OTG current setting) to comply with the USB PD 3.0 PPS specifications.

If there is no external load on the USB OTG port and the system is powered by battery-only, the V_{MIN} Active Protection (VAP) feature is supported. In VAP, the VBUS voltage is charged up by the battery and the energy is stored in the input decoupling capacitors. When the system requires peak power spike, the charge stored on the input capacitor discharges to maintain the system voltage at minimum system voltage.

Adapter current, battery current and system power are monitored in SGM41570. When the system power is too high and exceeds available power from adapter and battery together, a flexibly programmed nPROCHOT pulse is asserted to inform CPU for throttle back.

PACKAGE/ORDERING INFORMATION

| M | ODEL | PACKAGE DESCRIPTION | SPECIFIED TEMPERATURE RANGE | ORDERING NUMBER | PACKAGE MARKING | PACKING OPTION | |
|-----|--------|------------------------|-----------------------------------|--------------------|-----------------------------|---------------------|--|
| SGI | M41570 | TQFN-4×4-32AL | -40°C to +125°C | SGM41570XTSE32G/TR | SGM41570 XTSE32 XXXXX | Tape and Reel, 3000 | |

MARKING INFORMATION

NOTE: XXXXX = Date Code, Trace Code and Vendor Code.



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

| Voltage Range (with Respect to GND) SRN, SRP, ACN, ACP, VBUS, VSYS | |
|--|---------------|
| SW1, SW2 BTST1, BTST2, HIDRV1, HIDRV2, nBAT | |
| | |
| LODBV4 LODBV2 (25mc) | |
| LODRV1, LODRV2 (25ns) | |
| HIDRV1, HIDRV2 (25ns) | |
| SW1, SW2 (25ns) | |
| SDA, SCL, REGN, CHRG_OK, OTG/VAP | _ |
| CELL_BATPRESZ, LODRV1, LODRV2, n | |
| CMPOUT | |
| COMP1, COMP2 | |
| IADPT, IBAT, PSYS | 0.3V to 3.6V |
| Differential Voltage Range | |
| BTST1-SW1, BTST2-SW2, HIDRV1-SW | 1, HIDRV2-SW2 |
| | 0.3V to 7V |
| SRP-SRN, ACP-ACN | 0.5V to 0.5V |
| Package Thermal Resistance | |
| TQFN-4×4-32AL, θ _{JA} | 36°C/W |
| Junction Temperature | +150°C |
| Storage Temperature Range | |
| Lead Temperature (Soldering, 10s) | |
| ESD Susceptibility | |
| HBM | +5000\/ |
| | |
| CDM | ±1000V |

OVERSTRESS CAUTION

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

RECOMMENDED OPERATING CONDITIONS

| Voltage Range (with Respect to GND) |
|--|
| ACN, ACP, VBUS0V to 24V |
| SRN, SRP, VSYS0V to 19.2V |
| SW1, SW22V to 24V |
| BTST1, BTST2, HIDRV1, HIDRV2, nBATDRV |
| 0V to 30V |
| SDA, SCL, CHRG_OK, COMP1, COMP2, CMPIN, |
| CMPOUT, nPROCHOT |
| |
| CELL_BATPRESZ, ILIM_HIZ, LODRV1, LODRV2, VDDA, |
| REGN |
| IADPT, IBAT, PSYS0V to 3.3V |
| Differential Voltage Range |
| BTST1-SW1, BTST2-SW2, HIDRV1-SW1, HIDRV2-SW2 |
| 0V to 6V |
| SRP-SRN, ACP-ACN0.5V to 0.5V |
| Operating Junction Temperature Range40°C to +125°C |

ESD SENSITIVITY CAUTION

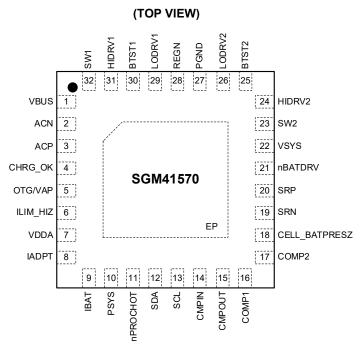
This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.



PIN CONFIGURATION



TQFN-4×4-32AL

PIN DESCRIPTION

| PIN | NAME | TYPE (1) | FUNCTION | | |
|-----|----------|----------|---|--|--|
| 1 | VBUS | Р | Charger Input. Place an RC low pass filter on this pin (R = 1Ω and C $\ge 0.47\mu$ F). | | |
| 2 | ACN | Р | Negative Terminal of the Input Current Sense Resistor. Place an RC low pass filter between this pin and the sense resistor. | | |
| 3 | ACP | Р | Positive Terminal of the Input Current Sense Resistor. Place an RC low pass filter between this pin and the sense resistor. | | |
| 4 | CHRG_OK | 0 | Active High Open-Drain Good Power Source Status Output. Place a $10k\Omega$ resistor between this pin and pull-up rail. CHRG_OK goes high with no fault (SYS short latch off, SYSOVP, BATOC, ACOC, force latch off, and thermal shutdown) when VBUS voltage rises above V_{VBUS_CONVEN} or falls below V_{ACOV} . CHRG_OK goes low when VBUS falls below V_{VBUS_CONVEN} or rises above V_{ACOV} or when above fault occurs. | | |
| 5 | OTG/VAP | 1 | OTG or VAP Modes Enable Input (Active High). OTG mode enable: OTG_VAP_MODE bit = 1, EN_OTG bit = 1 and pull this pin to high. VAP mode enable: OTG_VAP_MODE bit = 0, and pull this pin to high. | | |
| 6 | ILIM_HIZ | _ | Input Current Limit Setting Input. Connect this pin to a resistor divider between supply and ground to set the target input current limit I_{DPM} using the following equation: $V_{ILIM_HIZ} = 1V + 40 \times I_{DPM} \times R_{AC}$ The actual input current limit is the lower setting of ILIM_HIZ pin and IIN_HOST register. The device enters | | |
| 7 | 7 VDDA P | | HIZ mode when $V_{\text{ILIM_HIZ}} < 0.6V$, and exits HIZ mode when $V_{\text{ILIM_HIZ}} > 0.83V$. Internal Reference Bias. Place a 10Ω resistor from REGN to this pin, and place a $1\mu\text{F}$ ceramic capacitor from this pin to ground. | | |
| 8 | IADPT | 0 | Adapter Current Monitoring Output. V_{IADPT} = 20 or 40 × (V_{ACP} - V_{ACN}) and 20V/V or 40V/V can be selected in the IADPT_GAIN bit. Place a resistor from this pin to ground according to Inductance Detection through IADPT Pin section. The resistor is 137k Ω when L = 2.2 μ H. Connect a 100pF or less ceramic decoupling capacitor from this pin to ground. IADPT output voltage is clamped below 3.2V. | | |
| 9 | IBAT | 0 | Battery Current Monitoring Output. The charge current is monitored as $V_{IBAT} = 8$ or $16 \times (V_{SRP} - V_{SRN})$, and the discharge current is monitored as $V_{IBAT} = 8$ or $16 \times (V_{SRN} - V_{SRP})$. $8V/V$ or $16V/V$ can be selected in the IBAT_GAIN bit. Connect a 100pF or less ceramic decoupling capacitor from this pin to ground. IBAT pin can be left floating if not in use and its output voltage is clamped below 3.3V. | | |

PIN DESCRIPTION (continued)

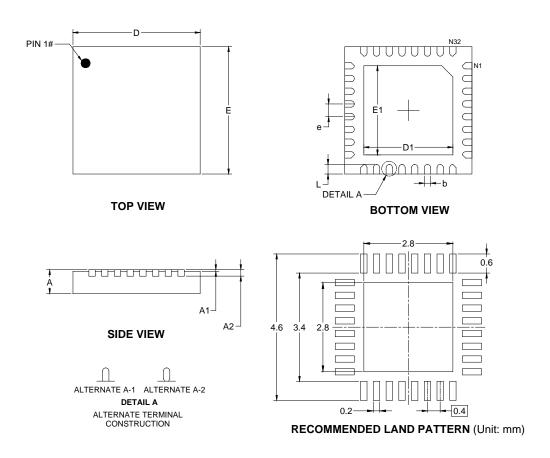
| PIN | NAME | TYPE (1) | FUNCTION |
|----------------|---------------|----------|--|
| 10 | PSYS | 0 | System Power Monitoring Output (Current Mode). The output current of this pin is proportional to the total power from the adapter and the battery refers to High-Accuracy Power Sense Amplifier (PSYS) section. The gain can be selected by SMBus. Connect a resistor between this pin and ground to generate output voltage. PSYS pin can be left floating if not in use. And its output voltage is clamped below 3.3V. |
| 11 | nPROCHOT | 0 | Active Low Open-Drain Processor Hot Indicator Output. The adapter input current, battery discharge current and system voltage are monitored, and a pulse is asserted if any event in the nPROCHOT profile is triggered. The minimum pulse width is adjustable in PROCHOT_WIDTH[1:0] bits. |
| 12 | SDA | I/O | SMBus Data Signal. Use a 10kΩ pull-up to the logic high rail. |
| 13 | SCL | I | SMBus Clock Signal. Use a $10k\Omega$ pull-up to the logic high rail. |
| 14 | CMPIN | I | Independent Comparator Input. The voltage sensed on this pin is compared with internal reference by the independent comparator, and the output of comparator is on CMPOUT pin. The internal reference, output polarity and deglitch time are all selectable in the SMBus host. When CMP_POL bit = 1, the internal hysteresis is determined by the resistor between CMPIN and CMPOUT. When CMP_POL bit = 0, the internal hysteresis is 110mV. Connect this pin to ground if the independent comparator is not in use. |
| 15 | CMPOUT | 0 | Open-Drain Independent Comparator Output. Place a resistor between this pin and pull-up supply rail. |
| 16 | COMP1 | I | Buck-Boost Compensation Pin 1. Refer to Figure 2 for the compensation network. |
| 17 | COMP2 | I | Buck-Boost Compensation Pin 2. Refer to Figure 2 for the compensation network. |
| 18 | CELL_BATPRESZ | ı | Battery Cell Selection Input. This pin is biased from VDDA, and sets the SYSOVP thresholds (5V for 1-cell, 12V for 2-cell, and 19.4V for 3-cell/4-cell). When the voltage on this pin is pulled below V _{CELL_BATPRESZ_FALL} , it indicates battery removal. The device exits LEARN mode, the charge current goes back to 0. And the MaxChargeVoltage/MinSystemVoltage register goes to default. |
| 19 | SRN | Р | Negative Input of the Charge Current Sense Resistor. This pin also senses the battery voltage. Place an optional 0.1µF ceramic capacitor from this pin to GND for common-mode noise filtering. Place a 0.1µF ceramic capacitor from SRP to SRN for differential mode noise filtering. |
| 20 | SRP | Р | Positive Input of the Charge Current Sense Resistor. Place an optional $0.1\mu F$ ceramic capacitor from this pin to GND for common-mode noise filtering. Place a $0.1\mu F$ ceramic capacitor from SRP to SRN for differential mode noise filtering. |
| 21 | nBATDRV | 0 | P-Channel BATFET Gate Driver Output. It is shorted to VSYS for turning off the BATFET and goes 11V below VSYS for fully on. |
| 22 | VSYS | Р | System Voltage Sensing. |
| 23 | SW2 | Р | Boost Mode Switching Node. Connect it to the source of the Boost mode high-side N-channel MOSFET (Q4). |
| 24 | HIDRV2 | 0 | Boost Mode High-side N-Channel MOSFET (Q4) Driver. Connect it to the gate of Q4. |
| 25 | BTST2 | Р | Boost Mode High-side N-Channel MOSFET (Q4) Driver Power Supply. Place a 47nF capacitor between SW2 and BTST2. It is internally connected to the boost-strap diode cathode. |
| 26 | LODRV2 | 0 | Boost Mode Low-side N-Channel MOSFET (Q3) Driver. Connect it to the gate of Q3. |
| 27 | PGND | GND | Power Ground. |
| 28 | REGN | Р | 5.6V LDO Output. It is supplied from VBUS or VSYS and the LDO is active when VBUS voltage is above $V_{\text{VBUS_CONVEN}}$. A 2.2 μ F or 3.3 μ F ceramic capacitor is recommended between this pin and PGND. |
| 29 | LODRV1 | 0 | Buck Mode Low-side N-Channel MOSFET (Q2) Driver. Connect it to the gate of Q2. |
| 30 | BTST1 | Р | Buck Mode High-side N-Channel MOSFET (Q1) Driver Power Supply. Place a 47nF capacitor between SW1 and BTST1. It is internally connected to the boost-strap diode cathode. |
| 31 | HIDRV1 | 0 | Buck Mode High-side N-Channel MOSFET (Q1) Driver. Connect it to the gate of Q1. |
| 32 | SW1 | Р | Buck Mode Switching Node. Connect it to the source of the Buck mode high-side N-channel MOSFET (Q1). |
| Exposed Pad | EP | - | Thermal Pad. It is the thermal pad to conduct heat from the device. Tie it externally to the PCB power ground plane. Thermal vias under the pad are needed to conduct the heat to the PCB power ground planes. |

NOTE:

1. I = Input, O = Output, I/O = Input or Output, P = Power.



PACKAGE OUTLINE DIMENSIONS TQFN-4×4-32AL



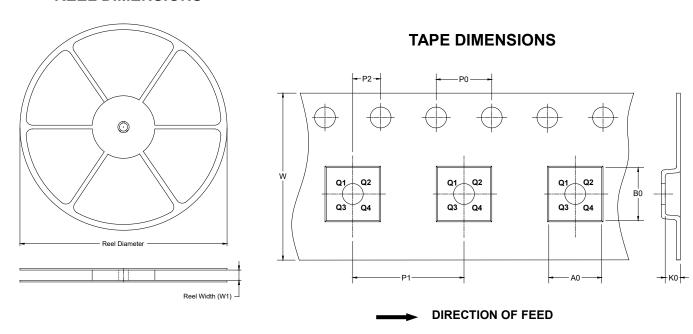
| Symbol | Dimensions In Millimeters | | | | | | |
|--------|---------------------------------------|-----------|-------|--|--|--|--|
| Зушьог | MIN | MOD | MAX | | | | |
| Α | 0.700 | 0.750 | 0.800 | | | | |
| A1 | 0.000 | - | 0.050 | | | | |
| A2 | | 0.200 REF | | | | | |
| D | 3.900 | 4.000 | 4.100 | | | | |
| E | 3.900 | 4.000 | 4.100 | | | | |
| D1 | 2.700 2.800 2.700 2.800 | | 2.900 | | | | |
| E1 | | | 2.900 | | | | |
| b | 0.150 | 0.200 | 0.250 | | | | |
| е | 0.400 BSC | | | | | | |
| L | 0.250 | 0.350 | | | | | |

NOTE: This drawing is subject to change without notice.



TAPE AND REEL INFORMATION

REEL DIMENSIONS

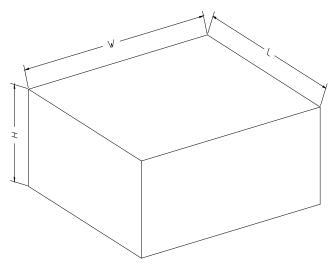


NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

| Package Type | Reel Diameter | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P0 (mm) | P1 (mm) | P2 (mm) | W (mm) | Pin1 Quadrant |
|---------------|------------------|--------------------------|------------|------------|------------|------------|------------|------------|-----------|------------------|
| TQFN-4×4-32AL | 13" | 12.4 | 4.30 | 4.30 | 1.10 | 4.0 | 8.0 | 2.0 | 12.0 | Q2 |

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

| Reel Type | | Length (mm) | Width (mm) | Height (mm) | Pizza/Carton | | |
|-----------|-----|----------------|---------------|----------------|--------------|--------|--|
| | 13" | 386 | 280 | 370 | 5 | DD0002 | |